RoHS Compliant

16GB DDR4 SDRAM SO-DIMM Halogen free

Product Specifications

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Version 0.4

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General Description

Apacer **D22.27261S.001** is a 2048M x 64 DDR4 SDRAM (Synchronous DRAM) SO-DIMM. This high-density memory module consists of 16 pieces 1024M x 8 bits DDR4 synchronous DRAMs in FBGA packages and a 4K Bits EEPROM. The module is a 260-pins dual in-line memory module and is intended for mounting into a connector socket. The following provides general specifications of this module.

Ordering Information

Part Number	Bandwidth	Speed Grade	Max Frequency	CAS Latency
D22.27261S.001	25.6 GB/sec	3200 Mbps	1600 MHz	CL22

Density	Organization	Component	Rank
16GB	2048M x 64	1024M x8*16	2

Key Parameters

MT/s	DDR4-2400	DDR4-2666	DDR4-2933	DDR4-3200	
Grade	-CL17	-CL19	-CL21	-CL22	Unit
tCK (min)	0.83	0.75	0.68	0.62	ns
CAS latency	17	19	21	22	tCK
tRCD (min)	14.16	14.25	14.32	13.75	ns
tRP (min)	14.16	14.25	14.32	13.75	ns
tRAS (min)	32	32	32	32	ns
tRC (min)	46.16	46.25	46.32	45.75	ns
CL-tRCD-tRP	17-17-17	19-19-19	21-21-21	22-22-22	tCK

Specifications:

- On-DIMM thermal sensor : No

- Organization: 2048 words x 64 bits, 2 ranks

- Integrating 16 pieces of 8G bits DDR4 SDRAM sealed FBGA

- Package: 260-pin socket type small outline dual in-line memory module (SO-DIMM)

- PCB: height 30.00 mm, lead pitch 0.50 mm (pin),

- Serial Presence Detect (SPD)

- Power Supply: VDD=1.2V (1.14V to 1.26V)

- VDDQ = 1.2V (1.14V to 1.26V)

- VPP = 2.5V (2.375V to 2.75V)

- VDDSPD = 2.2V to 3.6V

- 16 internal banks

- CAS Latency (CL): 10, 11, 12, 13, 14, 15,16,17,18,19, 20, 21, 22,24

- CAS Write Latency (CWL): 16,20

- Average refresh period

  7.8us at 0°C $\leqq$ TC $\leqq$ 85°C

  3.9us at 85°C $\leqq$ TC $\leqq$ 95°C

- Lead-free (RoHS compliant)

- Halogen free

Features:

- ♦ Functionality and operations comply with the DDR4 SDRAM datasheet

- ♦ Bank Grouping is applied, and CAS to CAS latency (tCCD_L, tCCD_S) for the banks in the same or different bank group accesses are available

- ♦ Bi-Directional Differential Data Strobe

- ♦ 8 bit pre-fetch

- ♦ Burst Length (BL) switch on-the-fly BL8 or BC4(Burst Chop)

- ♦ Per DRAM Addressability is supported

- ♦ Internal Vref DQ level generation is available

- ♦ Write CRC is supported at all speed grades

- ♦ DBI (Data Bus Inversion) is supported(x8)

- ♦ CA parity (Command/Address Parity) mode is supported
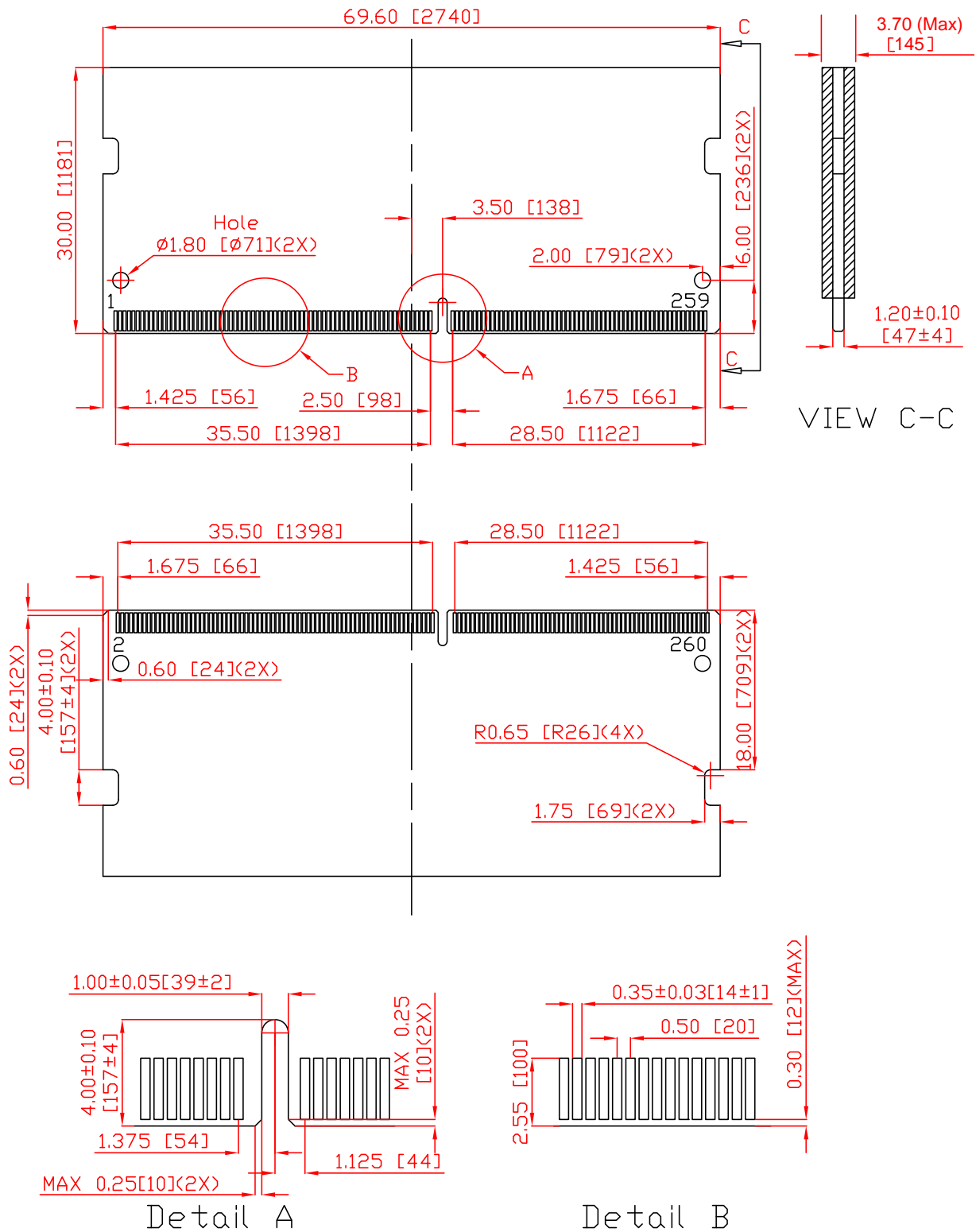
Environmental Requirements

Symbol	Parameter	Rating	Units	Notes
HOPR	Operating Humidity (relative)	10 to 90	%	
TSTG	Storage Temperature	-50 to +100	°C	1
HSTG	Storage Humidity (without condensation)	5 to 95	%	1
PBAR	Barometric Pressure (operating & storage)	105 to 69	kPa	1,2

Notes:

1. Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only. and device functional operation at or above the conditions indicated is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. Up to 9850 ft.

Mechanical Drawing

VIEW C-C

Detail A

Detail B

(All dimensions are in millimeters with ±0.15mm tolerance unless specified otherwise.)

Revision History

Revision	Date	Description	Remark
0.1	5/5/2014	Initial release	
0.2	11/2/2015	Updated VDDSPD	
0.3	03/15/2017	Add Environmental Requirements	
0.4	09/04/2017	Remove TOPR (Operating Temperature (ambient))	